

MMH75.16

Single-phase half-control

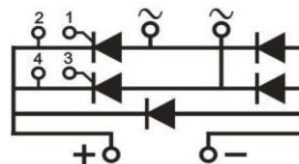
Features:

- International standard package
- Isolation voltage 2500V ~
- Simple mounting
- UL recognized, file no. E312789



Typical applications:

- Various rectifier power
- AC/DC motor control
- Heater control
- Light dimmer
- Frequency converters



Symbol	Characteristics	Test Conditions	Value			Unit
			Min	Typ	Max	
$V_{RSM/DSM}$	Non-repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			1700	V
$V_{RRM/DRM}$	Repetitive reverse/forward blocking voltage	$T_j = 25^{\circ}\text{C}$			1600	V
I_o	DC output current	Single-phase full wave rectifying circuit, $T_c = 85^{\circ}\text{C}$			75	A
I_{RRM} I_{DRM}	Repetitive peak current	at V_{DRM}/V_{RRM} $T_j = 125^{\circ}\text{C}$			10	mA
$I_{TSM} \cdot I_{FSM}$	Surge non repetitive current	10ms half sine wave $T_j = 45^{\circ}\text{C}$			1000	A
$I^2 t$	$I^2 t$ for fusing coordination	Thyristor: $V_R = 60\% V_{RRM}$ $T_j = 45^{\circ}\text{C}$			5000	A^2s
V_{TO}	Threshold voltage	$T_j = 125^{\circ}\text{C}$			0.90	V
r_T	On-state slope resistance	$T_j = 125^{\circ}\text{C}$			5	$\text{m}\Omega$
$V_{TM} \cdot V_{FM}$	Thyristor: Peak on-state voltage	$T = 25^{\circ}\text{C}$; $I_T = 90\text{A}$			1.60	V
	Diode: Peak forward voltage	$T = 25^{\circ}\text{C}$; $I_F = 90\text{A}$			1.20	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM} = 67\% V_{DRM}$, $T_j = 125^{\circ}\text{C}$, linear voltage rise			500	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of off-state current	$T_j = 25^{\circ}\text{C}$, Gate source 1,5A, $T_r < 0,5\mu\text{s}$			150	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current	$V_A = 12\text{V}$, $I_A = 1\text{A}$, $T_j = 25^{\circ}\text{C}$	20		150	mA
V_{GT}	Gate trigger voltage		0.70		1.80	V
I_{GD}	Gate non-trigger current	$V_D = 2/3 V_{DRM}$, $T_j = 125^{\circ}\text{C}$			10	mA
V_{GD}	Gate non-trigger voltage				0.25	V
P_{GM}	Gate peak power				10	W
$P_{G(AV)}$	Gate average power				0.5	W
I_H	Holding current	$T_j = 25^{\circ}\text{C}$	20		150	mA
I_L	Latching current	$T_j = 25^{\circ}\text{C}$	100		400	mA
$R_{th(j-c)}$	Thermal resistance junction to case	per module			0.47	$^{\circ}\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal resistance case to sink	per module			0.07	$^{\circ}\text{C}/\text{W}$
V_{ISO}	Isolation voltage	50Hz, RMS, $t = 1\text{min}$, $I_{ISO} : 1\text{mA (MAX)}$		2500		V
F_M	Mounting torque - copper plate (M6)		4		6	N·m
	Mounting torque - terminal (M5)		2.5		4.5	N·m
T_{stg}	Storage Temperature		-40		125	$^{\circ}\text{C}$
T_j	Operating Temperature		-40		125	$^{\circ}\text{C}$
W_t	Weight			190		g
Outline	M18-1					

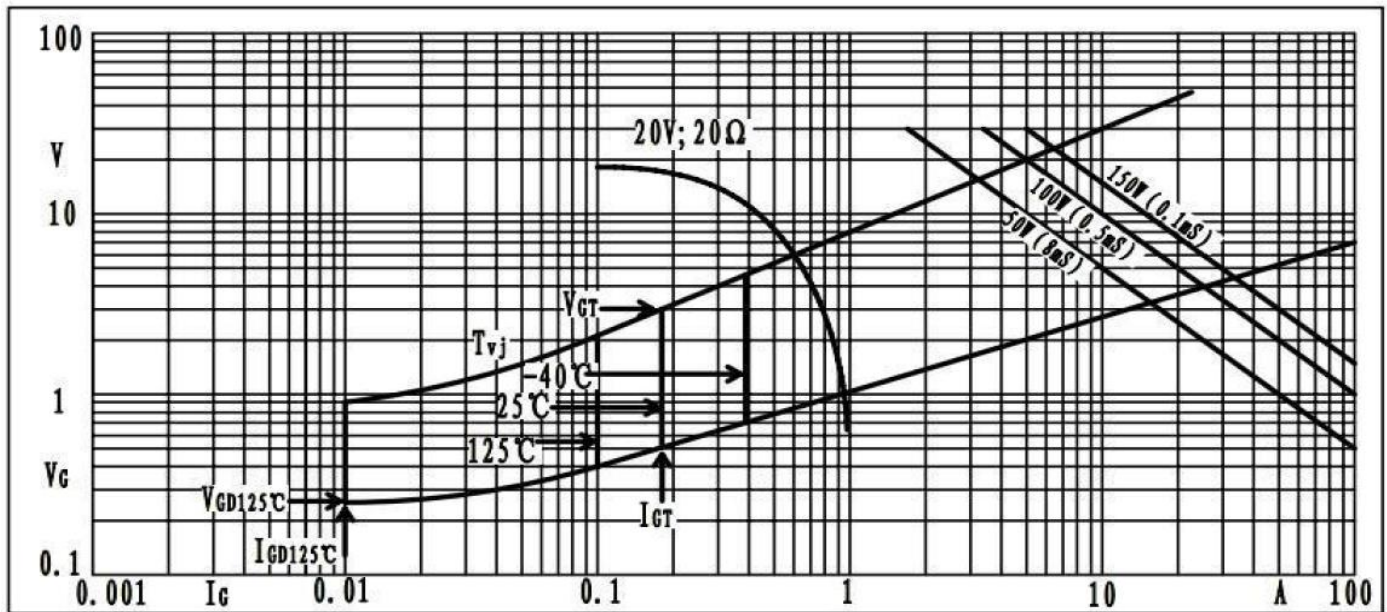


Fig1. Gate trigger characteristics

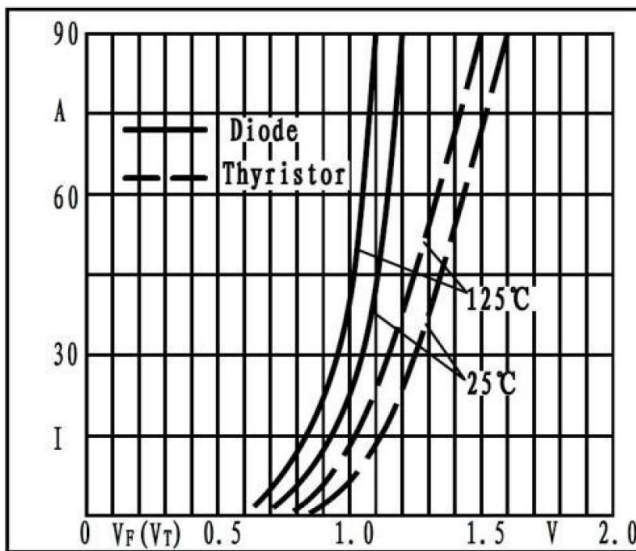


Fig2. Forward characteristics

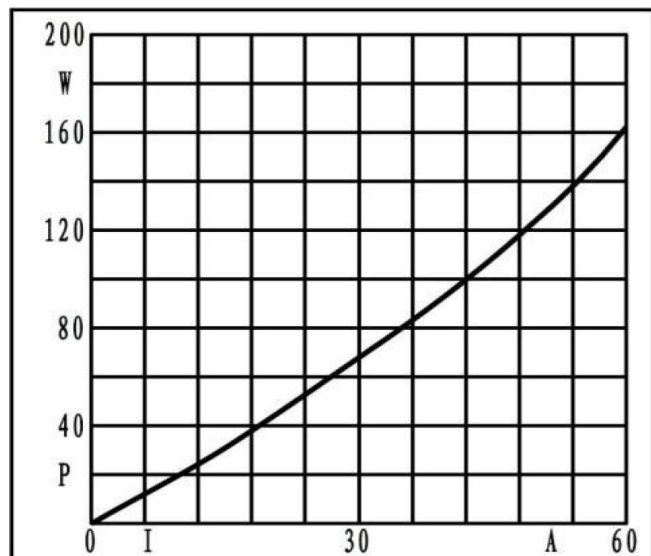


Fig3. Power dissipation

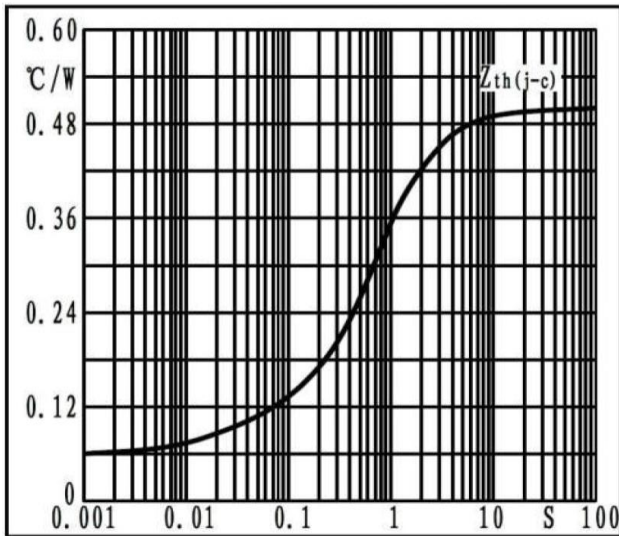


Fig4. Transient thermal impedance

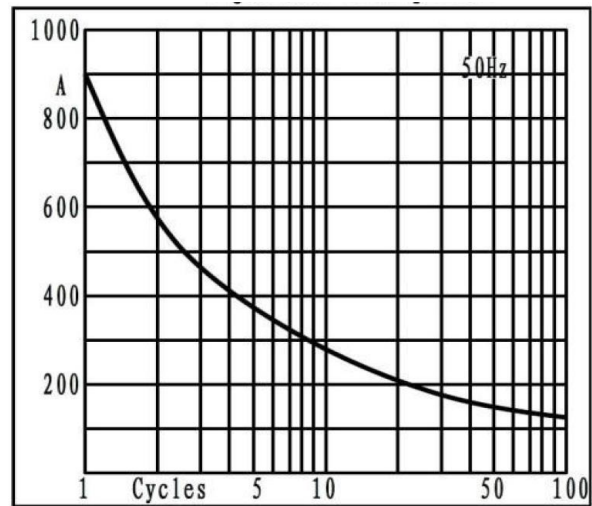


Fig5. Max non-repetitive forward surge current

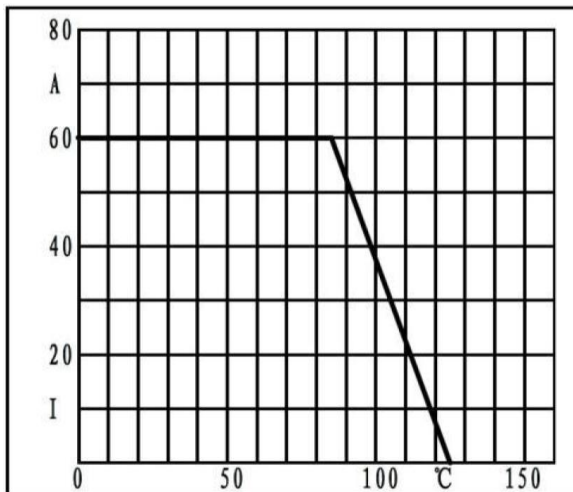
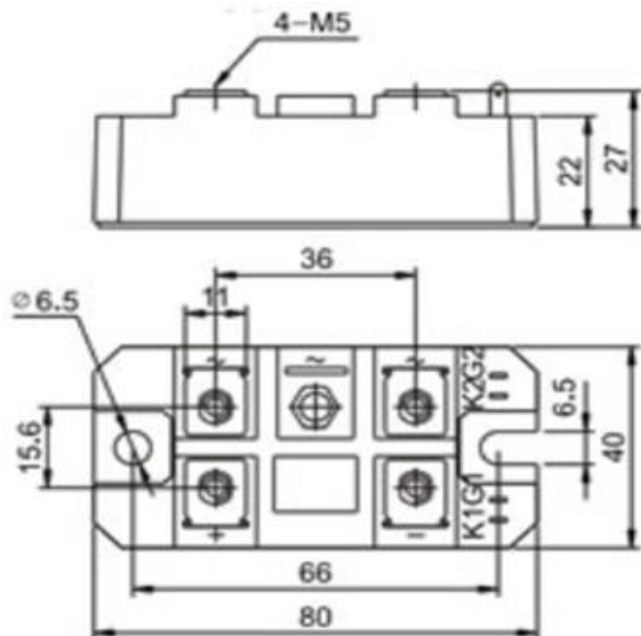


Fig6. Forward current derating curve



S.CO.M.E.S. Srl

Via Enrico Mattei, 6/8 - 26283 - Castiglione d'Adda (LO) - Italy

Phone: +39 0377 901243 Fax: +39 0377 900206